Thermal Atomic Layer Etching of SiO_2 by a "Conversion-Etch" Mechanism

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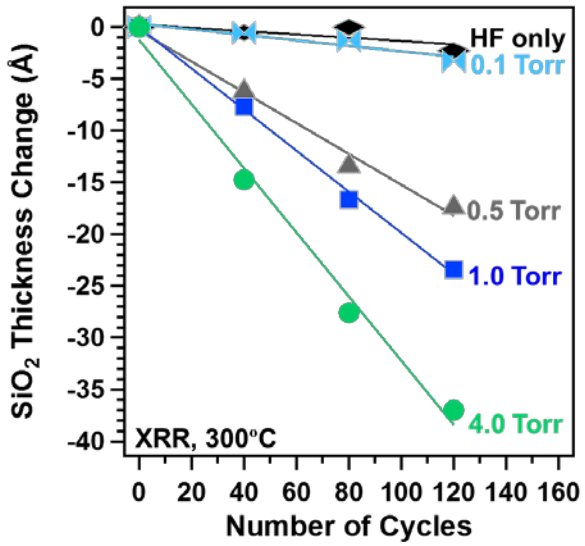

Figure S1. SiO_2 thickness change versus number of SiO_2 ALE cycles determined by XRR measurements at TMA/HF pressures of 0.1, 0.5, 1.0 and 4.0 Torr.

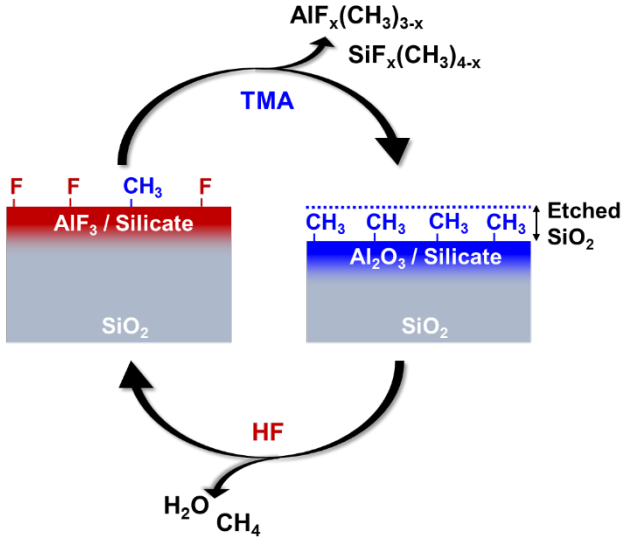

Figure S2. Schematic of "conversion-etch" reaction mechanism showing the sequential TMA and HF reactions.